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ΡΛΝ	JIT
	SEMI
	CONDUCTOR

PJQ4476AP

100V N-Channel Enhancement Mode MOSFET DFN3333-8L

Voltage

Current 35 A

03

Features

- R_{DS(ON)}, V_{GS}@10V, I_D@15A<25mΩ
- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<28.5mΩ

100 V

- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.001 ounces, 0.03 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	100	N	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	Tc=25°C	- I _D	35	А	
Continuous Drain Current ^(Note 4)	Tc=100°C		22		
Pulsed Drain Current ^(Note 1)	Tc=25°C	I _{DM}	140		
Dower Dissipation	Tc=25°C	PD	62	W	
Power Dissipation	Tc=100°C		25		
Continuous Drain Current(Note 4)	T _A =25°C	ID	6.3	A	
Continuous Drain Current ^(Note 4)	T _A =70°C		5		
Dower Dissipation	T _A =25°C	Pd	2.0	W	
Power Dissipation	T _A =70°C		1.3		
Single Pulse Avalanche Energy ^(Note 6)		E _{AS}	54	mJ	
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~150	٥C	
	Junction to Case	R _{θJC}	2	°C/W	
Typical Thermal Resistance ^(Note 4,5)	Junction to Ambient	R _{0JA}	62.5		



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static		1					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100	-	-	v	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	1.73	2.5	v	
Desia Course On Otata Desistance		V _{GS} =10V, I _D =15A	-	20	25		
Drain-Source On-State Resistance	RDS(on)	V _{GS} =4.5V, I _D =10A	-	22	28.5	mΩ	
Zero Gate Voltage Drain Current	IDSS	V _{DS} =80V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	lgss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 5)							
Total Gate Charge	Qg		-	31	-		
Gate-Source Charge	Q _{gs}	V _{DS} =50V, I _D =10A, V _{GS} =10V ^(Note 2,3)	-	5.1	-	nC	
Gate-Drain Charge	Q _{gd}		-	7.3	-		
Input Capacitance	Ciss		-	1519	-	pF	
Output Capacitance	Coss	$V_{DS}=30V, V_{GS}=0V,$	-	132	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	66	-		
Turn-On Delay Time	td _(on)	V _{DD} =50V, I _D =10A, V _{GS} =10V,	-	11	-		
Turn-On Rise Time	tr		-	42	-		
Turn-Off Delay Time	td _(off)		-	40	-	ns	
Turn-Off Fall Time	t _f	$R_G=3\Omega^{(Note 2,3)}$	-	19	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	Is		-	-	35	А	
Diode Forward Current	15			_	- 55		
Reverse Recovery Time	V _{SD}	Is=1A, V _{GS} =0V	-	0.68	1.2	V	

NOTES :

- 1. Pulse width
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=3mH, I_{AS}=6A, V_{DD}=50V, V_{GS}=10V, Starting T_J=25^{\circ}C.
- 7. Guaranteed by design, not subject to production testing.

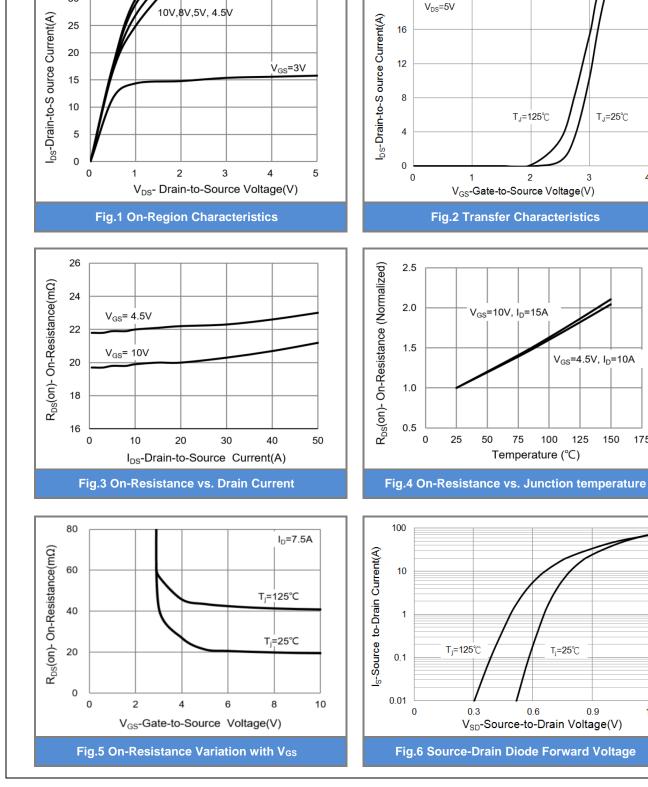
SEMI CONDUCTOR

PANJ

30

PJQ4476AP

TYPICAL CHARACTERISTIC CURVES



T_=25℃

150

175

4

20

1.2



PJQ4476AP

TYPICAL CHARACTERISTIC CURVES 10 V_{DS}=50V V_{GS}-Gate-to-Source Voltage(V) I_D=10A 8 6 4 2 0 0 8 16 24 32 Qg(nC)



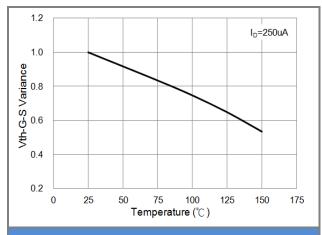
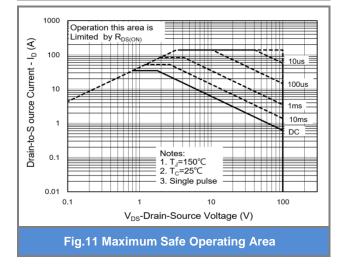
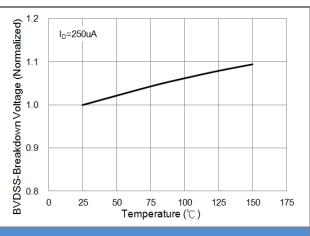
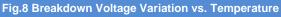
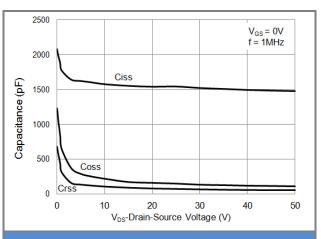


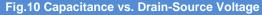
Fig.9 Threshold Voltage Variation with Temperature

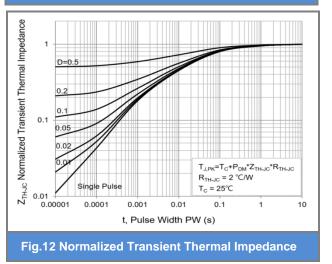












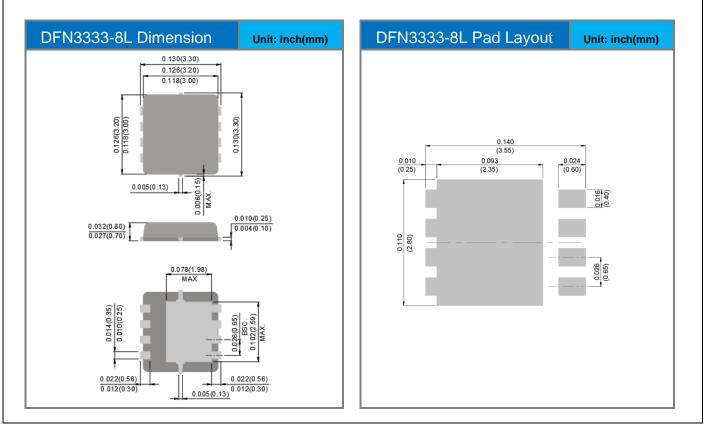


Part No. Packing Code Version

PJQ4476AP

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4476AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4476	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout





PJQ4476AP

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